



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	7.5Ω @ V _{GS} = 5V	210mA

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Power Management Functions

Features and Benefits

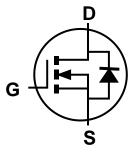
- N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

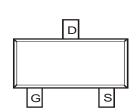
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe.
 Solderable per MIL-STD-202, Method 208 (a)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)







Equivalent Circuit



Top View

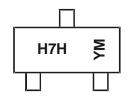
Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002H-7	SOT23	3,000/Tape & Reel
2N7002H-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



H7H = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021
Code	В	С	D	Е	F	G	Н	

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage		Continuous Pulsed	V _{GSS}	±20 ±40	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +85$ °C $T_A = +100$ °C	I _D	170 120 105	mA
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +85$ °C $T_A = +100$ °C	I _D	210 150 135	mA
Maximum Body Diode Forward Current (Note 6)		Continuous Pulsed	Is	0.5 2	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	1		I _{DM}	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	ב	370	mW
Total Power Dissipation	(Note 6)	P_D	510	IIIVV
Thermal Resistance, Junction to Ambient	(Note 5)	2	341	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	249	C/VV
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

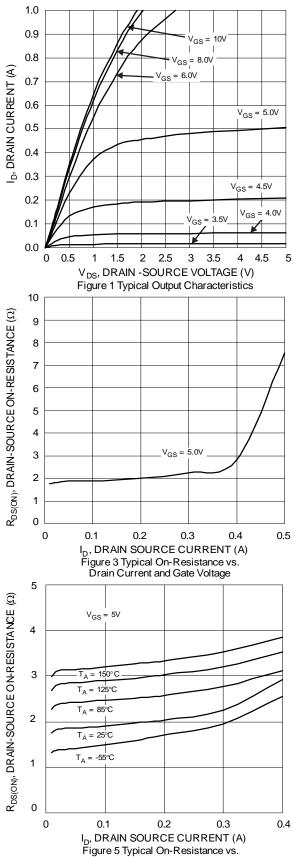
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

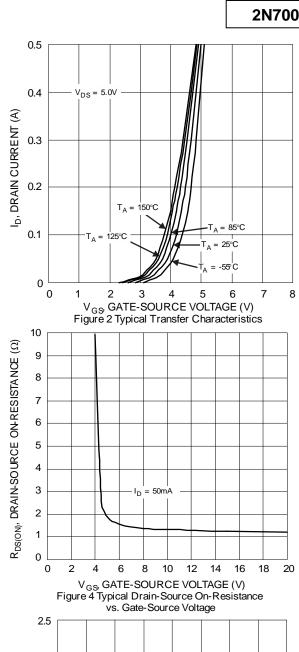
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60		_	V	$V_{GS} = 0V, I_{D} = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Body Leakage	lgss	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	2.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	3.0	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$	
Diode Forward Voltage	V _{SD}	_	0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		26	_	pF)/ OF)/)/ O)/	
Output Capacitance	Coss	_	2.8	_	pF	$V_{DS} = 25V, V_{GS} = 0V$ - f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	2.1	_	pF	1 = 1.0IVIDZ	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	352	_			
Gate-Source Charge	Q _{gs}	_	203	_	рС	$V_{DS} = 10V, I_D = 250mA$	
Gate-Drain Charge	Q_gd	_	123	_			
Turn-On Delay Time	t _{D(on)}	_	3.7	_			
Turn-On Rise Time	t _r		2.9			$V_{DD} = 30V, I_D = 0.2A,$	
Turn-Off Delay Time	t _{D(off)}	_	8.4	_	ns	$R_L = 150\Omega, V_{GEN} = 10V,$	
Turn-Off Fall Time	t _f	_	4.7	_		$R_{GEN} = 25\Omega$	
Body Diode Reverse Recovery Time	t _{rr}	-	9.3	-	ns	$I_S = 0.5A$, $dI/dt = 100A/\mu s$	
Body Diode Reverse Recovery Charge	Q _{rr}	-	3.5	-	nC	$I_S = 0.5A$, $dI/dt = 100A/\mu s$	

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.







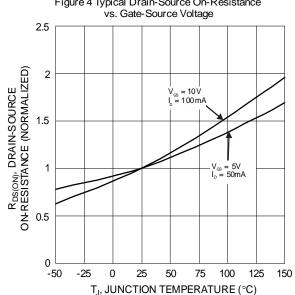
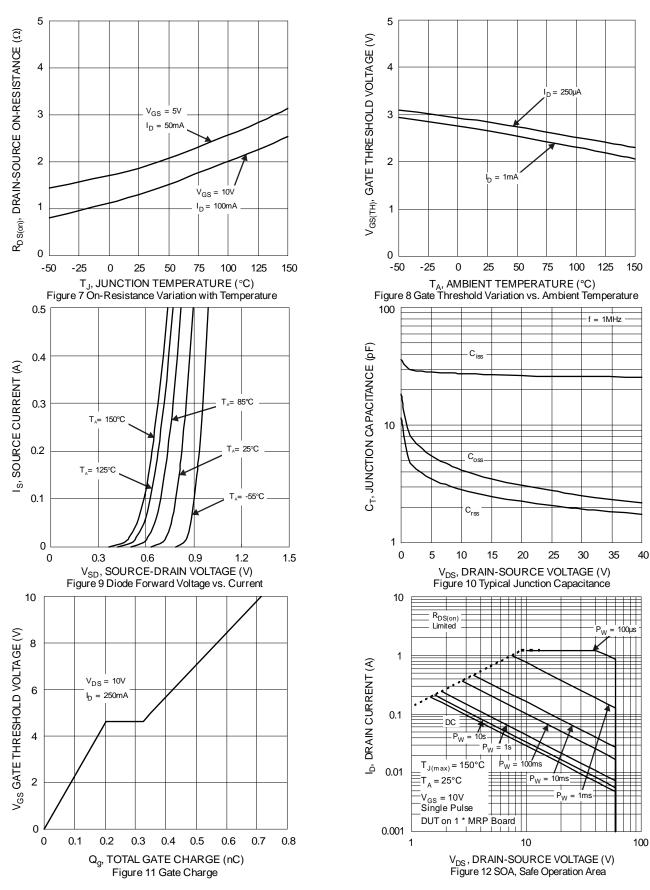


Figure 6 On-Resistance Variation with Temperature

Drain Current and Temperature







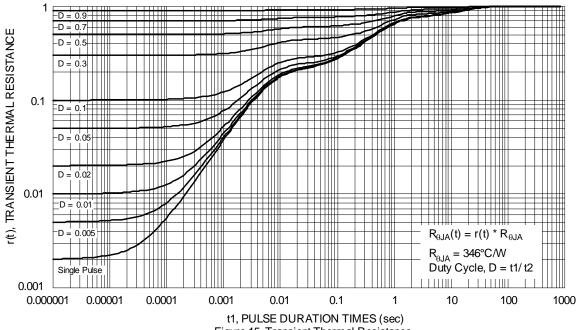
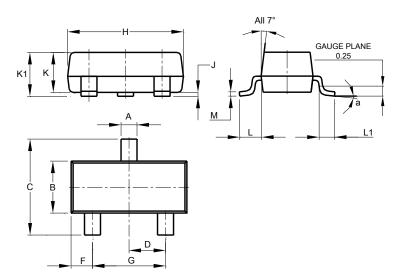


Figure 15 Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

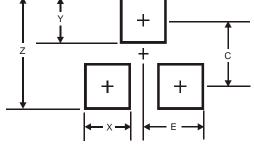


50123								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
M	0.085	0.150	0.110					
а	a 8°							
All	Dimens	ions in	mm					

SOT23

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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